

Colin Humphreys

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

309
papers

7,399
citations

45
h-index

73
g-index

321
ext. papers

8,081
ext. citations

3.9
avg, IF

5.87
L-index

#	Paper	IF	Citations
309	Wafer-Scale Graphene Anodes Replace Indium Tin Oxide in Organic Light-Emitting Diodes (Advanced Optical Materials 3/2022). <i>Advanced Optical Materials</i> , 2022 , 10, 2270012	8.1	
308	Wafer-Scale Graphene Anodes Replace Indium Tin Oxide in Organic Light-Emitting Diodes. <i>Advanced Optical Materials</i> , 2022 , 10, 2101675	8.1	1
307	Mechanical properties of graphene. <i>Applied Physics Reviews</i> , 2021 , 8, 021310	17.3	12
306	X-ray characterisation of the basal stacking fault densities of (112) GaN. <i>CrystEngComm</i> , 2021 , 23, 6059-6069	9.9	0
305	Unexpected softness of bilayer graphene and softening of A-A stacked graphene layers. <i>Physical Review B</i> , 2020 , 101,	3.3	6
304	Au-free recessed Ohmic contacts to AlGaIn/GaN high electron mobility transistor: Study of etch chemistry and metal scheme. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2020 , 38, 032207	1.3	2
303	A Novel Technique to Investigate the Role of Traps in the Off-State Performance of AlGaIn/GaN High Electron Mobility Transistor on Si Using Substrate Bias. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900794	1.6	1
302	Nanomechanics of graphene oxide-bacteriophage based self-assembled porous composites. <i>Scientific Reports</i> , 2020 , 10, 15618	4.9	4
301	Solution-Processed Epitaxial Growth of Arbitrary Surface Nanopatterns on Hybrid Perovskite Monocrystalline Thin Films. <i>ACS Nano</i> , 2020 , 14, 11029-11039	16.7	9
300	3D Strain in 2D Materials: To What Extent is Monolayer Graphene Graphite?. <i>Physical Review Letters</i> , 2019 , 123, 135501	7.4	26
299	Effect of Size on the Luminescent Efficiency of Perovskite Nanocrystals. <i>ACS Applied Energy Materials</i> , 2019 , 2, 6998-7004	6.1	5
298	Insight into the impact of atomic- and nano-scale indium distributions on the optical properties of InGaIn/GaN quantum well structures grown on m-plane freestanding GaN substrates. <i>Journal of Applied Physics</i> , 2019 , 125, 225704	2.5	3
297	Optical properties of c-Plane InGaIn/GaN single quantum wells as a function of total electric field strength. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCB09	1.4	3
296	Optical and structural properties of dislocations in InGaIn. <i>Journal of Applied Physics</i> , 2019 , 125, 165701	2.5	8
295	InGaIn as a Substrate for AC Photoelectrochemical Imaging. <i>Sensors</i> , 2019 , 19,	3.8	7
294	Effect of humidity on the interlayer interaction of bilayer graphene. <i>Physical Review B</i> , 2019 , 99,	3.3	12
293	Nanoscale structural and chemical analysis of F-implanted enhancement-mode InAlIn/GaN heterostructure field effect transistors. <i>Journal of Applied Physics</i> , 2018 , 123, 024902	2.5	2

292	Vertical leakage mechanism in GaN on Si high electron mobility transistor buffer layers. <i>Journal of Applied Physics</i> , 2018 , 124, 055702	2.5	20
291	Atomic Resolution Imaging of Dislocations in AlGaIn and the Efficiency of UV LEDs. <i>Microscopy and Microanalysis</i> , 2018 , 24, 4-5	0.5	
290	Alloy fluctuations at dislocations in III-nitrides: identification and impact on optical properties 2018 ,		1
289	What is red? On the chromaticity of orange-red InGaIn/GaIn based LEDs. <i>Journal of Applied Physics</i> , 2018 , 124, 183102	2.5	18
288	Recombination from polar InGaIn/GaIn quantum well structures at high excitation carrier densities. <i>Physical Review B</i> , 2018 , 98,	3.3	8
287	Effects of a Si-doped InGaIn Underlayer on the Optical Properties of InGaIn/GaIn Quantum Well Structures with Different Numbers of Quantum Wells. <i>Materials</i> , 2018 , 11,	3.5	5
286	Photomodulated Reflectivity Measurement of Free-Carrier Dynamics in InGaIn/GaIn Quantum Wells. <i>ACS Photonics</i> , 2018 , 5, 4437-4446	6.3	4
285	Effect of growth temperature and V/III-ratio on the surface morphology of MOVPE-grown cubic zincblende GaIn. <i>Journal of Applied Physics</i> , 2018 , 124, 105302	2.5	13
284	Effects of surface plasma treatment on threshold voltage hysteresis and instability in metal-insulator-semiconductor (MIS) AlGaIn/GaIn heterostructure HEMTs. <i>Journal of Applied Physics</i> , 2018 , 123, 184503	2.5	4
283	Effect of stacking faults on the photoluminescence spectrum of zincblende GaIn. <i>Journal of Applied Physics</i> , 2018 , 123, 185705	2.5	9
282	Evolution of the m-Plane Quantum Well Morphology and Composition within a GaIn/InGaIn CoreShell Structure. <i>Crystal Growth and Design</i> , 2017 , 17, 474-482	3.5	8
281	X-ray reflectivity method for the characterization of InGaIn/GaIn quantum well interface. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600664	1.3	5
280	Carrier localization in the vicinity of dislocations in InGaIn. <i>Journal of Applied Physics</i> , 2017 , 121, 013104	2.5	36
279	Structural and magnetic properties of ultra-thin Fe films on metal-organic chemical vapour deposited GaIn(0001). <i>Journal of Applied Physics</i> , 2017 , 121, 043904	2.5	5
278	The atomic structure of polar and non-polar InGaIn quantum wells and the green gap problem. <i>Ultramicroscopy</i> , 2017 , 176, 93-98	3.1	19
277	All-GaIn-Integrated Cascode Heterojunction Field Effect Transistors. <i>IEEE Transactions on Power Electronics</i> , 2017 , 32, 8743-8750	7.2	9
276	Structural impact on the nanoscale optical properties of InGaIn core-shell nanorods. <i>Applied Physics Letters</i> , 2017 , 110, 172105	3.4	19
275	Mechanisms preventing trench defect formation in InGaIn/GaIn quantum well structures using hydrogen during GaIn barrier growth. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600666	1.3	10

274	Photoluminescence studies of cubic GaN epilayers. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600733	1.3	13
273	Temperature and Bias Dependent Trap Capture Cross Section in AlGaIn/GaN HEMT on 6-in Silicon With Carbon-Doped Buffer. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 4868-4874	2.9	18
272	X-ray diffraction analysis of cubic zincblende III-nitrides. <i>Journal Physics D: Applied Physics</i> , 2017 , 50, 433002	3.0	26
271	Perspectives on Electronic and Photonic Materials. <i>Springer Handbooks</i> , 2017 , 1-1	1.3	0
270	Machine Learning Predicts Laboratory Earthquakes. <i>Geophysical Research Letters</i> , 2017 , 44, 9276-9282	4.9	150
269	Dislocations in AlGaIn: Core Structure, Atom Segregation, and Optical Properties. <i>Nano Letters</i> , 2017 , 17, 4846-4852	11.5	23
268	Automatized convergence of optoelectronic simulations using active machine learning. <i>Applied Physics Letters</i> , 2017 , 111, 043506	3.4	6
267	The ABC model of recombination reinterpreted: Impact on understanding carrier transport and efficiency droop in InGaIn/GaN light emitting diodes. <i>Journal of Applied Physics</i> , 2017 , 122, 234505	2.5	20
266	Dual barrier InAlN/AlGaIn/GaN-on-silicon high-electron-mobility transistors with Pt- and Ni-based gate stacks. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600835	1.6	1
265	Impact of high energy electrons on nitrides for nanocathodoluminescence 2016 , 1044-1045		
264	Structural and optical properties of (112 2) InGaIn quantum wells compared to (0001) and (112 0). <i>Semiconductor Science and Technology</i> , 2016 , 31, 085007	1.8	4
263	Dielectric response of wurtzite gallium nitride in the terahertz frequency range. <i>Solid State Communications</i> , 2016 , 247, 68-71	1.6	15
262	n-Type conductivity bound by the growth temperature: the case of Al _{0.72} Ga _{0.28} N highly doped by silicon. <i>Journal of Materials Chemistry C</i> , 2016 , 4, 8291-8296	7.1	4
261	A study of the optical and polarisation properties of InGaIn/GaN multiple quantum wells grown on -plane and -plane GaN substrates. <i>Science and Technology of Advanced Materials</i> , 2016 , 17, 736-743	7.1	5
260	High-quality III-nitride films on conductive, transparent (2 01)-oriented MgAl ₂ O ₃ using a GaN buffer layer. <i>Scientific Reports</i> , 2016 , 6, 29747	4.9	39
259	Determination of axial and lateral exciton diffusion length in GaN by electron energy dependent cathodoluminescence. <i>Journal of Applied Physics</i> , 2016 , 120, 085703	2.5	9
258	Investigation of indium gallium nitride facet-dependent nonpolar growth rates and composition for core-shell light-emitting diodes. <i>Journal of Nanophotonics</i> , 2016 , 10, 016010	1.1	14
257	Optimizing GaN (0001) hetero-epitaxial templates grown on (0001) sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 61-66	1.3	17

256	Structural and Optical Emission Uniformity of m-Plane InGaN Single Quantum Wells in CoreShell Nanorods. <i>Crystal Growth and Design</i> , 2016 , 16, 1907-1916	3.5	23
255	Solid-State Lighting Based on Light Emitting Diode Technology 2016 , 87-118		8
254	Nanocathodoluminescence reveals the mitigation of the Stark shift in InGaN quantum wells by silicon doping 2016 , 562-563		
253	Toward defect-free semi-polar GaN templates on pre-structured sapphire. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 834-839	1.3	5
252	Molecular beam epitaxy of free-standing bulk wurtzite Al _x Ga _{1-x} N layers using a highly efficient RF plasma source. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 217-220		1
251	Modelling the closely-coupled cascode switching process 2016 ,		1
250	Combined electrical and resonant optical excitation characterization of multi-quantum well InGaN-based light-emitting diodes. <i>AIP Advances</i> , 2016 , 6, 075108	1.5	2
249	Optimisation of GaN LEDs and the reduction of efficiency droop using active machine learning. <i>Scientific Reports</i> , 2016 , 6, 24862	4.9	32
248	Theoretical and experimental analysis of the photoluminescence and photoluminescence excitation spectroscopy spectra of m-plane InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , 2016 , 109, 223102	3.4	6
247	Control of threshold voltage in E-mode and D-mode GaN-on-Si metal-insulator-semiconductor heterostructure field effect transistors by in-situ fluorine doping of atomic layer deposition Al ₂ O ₃ gate dielectrics. <i>Applied Physics Letters</i> , 2016 , 108, 072901	3.4	15
246	Comparative studies of efficiency droop in polar and non-polar InGaN quantum wells. <i>Applied Physics Letters</i> , 2016 , 108, 252101	3.4	17
245	A comparison of the optical properties of InGaN/GaN multiple quantum well structures grown with and without Si-doped InGaN prelayers. <i>Journal of Applied Physics</i> , 2016 , 119, 055708	2.5	12
244	Dislocation core structures in (0001) InGaN. <i>Journal of Applied Physics</i> , 2016 , 119, 105301	2.5	13
243	The nature of carrier localisation in polar and nonpolar InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , 2016 , 119, 181505	2.5	56
242	The microstructure of non-polar a-plane (11 200) InGaN quantum wells. <i>Journal of Applied Physics</i> , 2016 , 119, 175703	2.5	19
241	Local carrier recombination and associated dynamics in m-plane InGaN/GaN quantum wells probed by picosecond cathodoluminescence. <i>Applied Physics Letters</i> , 2016 , 109, 232103	3.4	7
240	Nano-cathodoluminescence reveals the effect of electron damage on the optical properties of nitride optoelectronics and the damage threshold. <i>Journal of Applied Physics</i> , 2016 , 120, 165704	2.5	8
239	Toward defect-free semi-polar GaN templates on pre-structured sapphire (Phys. Status Solidi B 5/2016). <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 1024-1024	1.3	

238	Effect of QW growth temperature on the optical properties of blue and green InGaN/GaN QW structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 209-213		4
237	Investigating efficiency droop in InGaN/GaN quantum well structures using ultrafast time-resolved terahertz and photoluminescence spectroscopy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 252-255		
236	Growth and coalescence studies of oriented GaN on pre-structured sapphire substrates using marker layers. <i>Physica Status Solidi (B): Basic Research</i> , 2016 , 253, 46-53	1.3	15
235	Room temperature PL efficiency of InGaN/GaN quantum well structures with prelayers as a function of number of quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 248-251		7
234	Effect of electron blocking layers on the conduction and valence band profiles of InGaN/GaN LEDs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 262-265		1
233	A study of the inclusion of prelayers in InGaN/GaN single- and multiple-quantum-well structures. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 866-872	1.3	14
232	Carrier distributions in InGaN/GaN light-emitting diodes. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 890-894	1.3	5
231	Enhancement-mode metal-insulator-semiconductor GaN/AlInN/GaN heterostructure field-effect transistors on Si with a threshold voltage of +3.0 V and blocking voltage above 1000 V. <i>Applied Physics Express</i> , 2015 , 8, 036502	2.4	8
230	SCM and SIMS investigations of unintentional doping in III-nitrides. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 403-407		6
229	Nanocathodoluminescence Reveals Mitigation of the Stark Shift in InGaN Quantum Wells by Si Doping. <i>Nano Letters</i> , 2015 , 15, 7639-43	11.5	28
228	Effect of the barrier growth mode on the luminescence and conductivity micron scale uniformity of InGaN light emitting diodes. <i>Journal of Applied Physics</i> , 2015 , 117, 115705	2.5	7
227	A study of the impact of in-situ argon plasma treatment before atomic layer deposition of Al ₂ O ₃ on GaN based metal oxide semiconductor capacitor. <i>Microelectronic Engineering</i> , 2015 , 147, 277-280	2.5	3
226	Structural, electronic, and optical properties of m-plane InGaN/GaN quantum wells: Insights from experiment and atomistic theory. <i>Physical Review B</i> , 2015 , 92,	3.3	48
225	Difference in linear polarization of biaxially strained In _x Ga _{1-x} N alloys on nonpolar a-plane and m-plane GaN. <i>Physical Review B</i> , 2015 , 92,	3.3	3
224	Effects of quantum well growth temperature on the recombination efficiency of InGaN/GaN multiple quantum wells that emit in the green and blue spectral regions. <i>Applied Physics Letters</i> , 2015 , 107, 132106	3.4	48
223	Dislocation core structures in Si-doped GaN. <i>Applied Physics Letters</i> , 2015 , 107, 243104	3.4	12
222	Impact of thermal treatment on the optical performance of InGaN/GaN light emitting diodes. <i>AIP Advances</i> , 2015 , 5, 107121	1.5	1
221	Enhancement mode operation in AlInN/GaN (MIS)HEMTs on Si substrates using a fluorine implant. <i>Semiconductor Science and Technology</i> , 2015 , 30, 105007	1.8	12

220	Optical studies of non-polar m-plane () InGaN/GaN multi-quantum wells grown on freestanding bulk GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 965-970	1.3	13
219	Segregation of In to dislocations in InGaN. <i>Nano Letters</i> , 2015 , 15, 923-30	11.5	49
218	Investigation of unintentional indium incorporation into GaN barriers of InGaN/GaN quantum well structures. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 928-935	1.3	14
217	Characteristics and applications of micro-pixelated GaN-based light emitting diodes on Si substrates. <i>Journal of Applied Physics</i> , 2014 , 115, 033112	2.5	80
216	Direct observation of depth-dependent atomic displacements associated with dislocations in gallium nitride. <i>Physical Review Letters</i> , 2014 , 113, 135503	7.4	21
215	Dislocation-related trap levels in nitride-based light emitting diodes. <i>Applied Physics Letters</i> , 2014 , 104, 211102	3.4	16
214	Effects of an InGaN prelayer on the properties of InGaN/GaN quantum well structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 710-713		10
213	High excitation density recombination dynamics in InGaN/GaN quantum well structures in the droop regime. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 694-697		1
212	The effects of varying threading dislocation density on the optical properties of InGaN/GaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 750-753		8
211	Correlating electroluminescence characterization and physics-based models of InGaN/GaN LEDs: Pitfalls and open issues. <i>AIP Advances</i> , 2014 , 4, 067118	1.5	23
210	Coincident electron channeling and cathodoluminescence studies of threading dislocations in GaN. <i>Microscopy and Microanalysis</i> , 2014 , 20, 55-60	0.5	23
209	Growth of non-polar (11-20) InGaN quantum dots by metal organic vapour phase epitaxy using a two temperature method. <i>APL Materials</i> , 2014 , 2, 126101	5.7	16
208	How Cutting-Edge Atomic Resolution Microscopy Can Help to Solve Some of the World's Energy Problems. <i>Microscopy and Microanalysis</i> , 2014 , 20, 11-14	0.5	
207	Microscopic, electrical and optical studies on InGaN/GaN quantum wells based LED devices 2014 ,		1
206	Carrier capture efficiency in InGaN/GaN LEDs: Role of high temperature annealing 2014 ,		3
205	Polarized photoluminescence excitation spectroscopy of a-plane InGaN/GaN multiple quantum wells grown on r-plane sapphire. <i>Journal of Applied Physics</i> , 2014 , 115, 113106	2.5	11
204	The effects of Si-doped prelayers on the optical properties of InGaN/GaN single quantum well structures. <i>Applied Physics Letters</i> , 2014 , 105, 092106	3.4	16
203	The impact of trench defects in InGaN/GaN light emitting diodes and implications for the green gap problem. <i>Applied Physics Letters</i> , 2014 , 105, 112110	3.4	39

202	Low temperature carrier redistribution dynamics in InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , 2014 , 115, 113505	2.5	16
201	Structure and strain relaxation effects of defects in In _x Ga _{1-x} N epilayers. <i>Journal of Applied Physics</i> , 2014 , 116, 103513	2.5	31
200	The impact of growth parameters on trench defects in InGaN/GaN quantum wells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 740-743	1.6	6
199	Dynamics of carrier redistribution processes in InGaN/GaN quantum well structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 738-741		2
198	Composition and luminescence studies of InGaN epilayers grown at different hydrogen flow rates. <i>Semiconductor Science and Technology</i> , 2013 , 28, 065011	1.8	12
197	The impact of gross well width fluctuations on the efficiency of GaN-based light emitting diodes. <i>Applied Physics Letters</i> , 2013 , 103, 141114	3.4	45
196	Prospects of III-nitride optoelectronics grown on Si. <i>Reports on Progress in Physics</i> , 2013 , 76, 106501	14.4	205
195	Elastic constants and critical thicknesses of ScGaN and ScAlN. <i>Journal of Applied Physics</i> , 2013 , 114, 243516		64
194	Correlations between the morphology and emission properties of trench defects in InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , 2013 , 113, 073505	2.5	28
193	High excitation carrier density recombination dynamics of InGaN/GaN quantum well structures: Possible relevance to efficiency droop. <i>Applied Physics Letters</i> , 2013 , 102, 022106	3.4	27
192	Properties of trench defects in InGaN/GaN quantum well structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2013 , 210, 195-198	1.6	12
191	The effect of dislocations on the efficiency of InGaN/GaN solar cells. <i>Solar Energy Materials and Solar Cells</i> , 2013 , 117, 279-284	6.4	29
190	The significance of Bragg's law in electron diffraction and microscopy, and Bragg's second law. <i>Acta Crystallographica Section A: Foundations and Advances</i> , 2013 , 69, 45-50		15
189	The impact of substrate miscut on the morphology of InGaN epitaxial layers subjected to a growth interruption. <i>Journal of Applied Physics</i> , 2013 , 113, 063503	2.5	7
188	Nanoscale-accuracy transfer printing of ultra-thin AlInGaN light-emitting diodes onto mechanically flexible substrates. <i>Applied Physics Letters</i> , 2013 , 103, 253302	3.4	43
187	Tunable optoelectronic and ferroelectric properties in Sc-based III-nitrides. <i>Journal of Applied Physics</i> , 2013 , 114, 133510	2.5	84
186	Mg doping affects dislocation core structures in GaN. <i>Physical Review Letters</i> , 2013 , 111, 025502	7.4	45
185	Interfacial structure and chemistry of GaN on Ge(111). <i>Physical Review Letters</i> , 2013 , 111, 256101	7.4	5

184	Carrier Density Dependent Localization and Consequences for Efficiency Droop in InGaN/GaN Quantum Well Structures. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JK10	1.4	13
183	The dissociation of the [a + c] dislocation in GaN. <i>Philosophical Magazine</i> , 2013 , 93, 3925-3938	1.6	29
182	On the origin of blue-green emission from heteroepitaxial nonpolar a-plane InGaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 465-468		4
181	The consequences of high injected carrier densities on carrier localization and efficiency droop in InGaN/GaN quantum well structures. <i>Journal of Applied Physics</i> , 2012 , 111, 083512	2.5	90
180	High-efficiency InGaN/GaN quantum well structures on large area silicon substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 13-16	1.6	10
179	Growth, microstructure and morphology of epitaxial ScGaN films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 33-40	1.6	14
178	Measurement of the Al content in AlGaIn epitaxial layers by combined energy-dispersive X-ray and electron energy-loss spectroscopy in a transmission electron microscope. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1079-1082		6
177	Studies of efficiency droop in GaN based LEDs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 765-769		4
176	Electron holography of an in-situ biased GaN-based LED. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 704-707		6
175	Recombination mechanisms in heteroepitaxial non-polar InGaIn/GaN quantum wells. <i>Journal of Applied Physics</i> , 2012 , 112, 013534	2.5	3
174	Structure and chemistry of the Si(111)/AlN interface. <i>Applied Physics Letters</i> , 2012 , 100, 011910	3.4	54
173	Morphological, structural, and emission characterization of trench defects in InGaIn/GaN quantum well structures. <i>Applied Physics Letters</i> , 2012 , 101, 212107	3.4	62
172	Atom probe tomography characterisation of a laser diode structure grown by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2012 , 111, 053508	2.5	11
171	Determination of the composition and thickness of semi-polar and non-polar III-nitride films and quantum wells using X-ray scattering. <i>Journal of Applied Physics</i> , 2012 , 111, 043502	2.5	13
170	Efficiency measurement of GaN-based quantum well and light-emitting diode structures grown on silicon substrates. <i>Journal of Applied Physics</i> , 2011 , 109, 014502	2.5	37
169	The effects of Si doping on dislocation movement and tensile stress in GaN films. <i>Journal of Applied Physics</i> , 2011 , 109, 073509	2.5	51
168	Response to Comment on The effects of Si doping on dislocation movement and tensile stress in GaN films[J. Appl. Phys. 109, 073509 (2011)]. <i>Journal of Applied Physics</i> , 2011 , 110, 096102	2.5	3
167	Carrier localization mechanisms in In _x Ga _{1-x} N/GaN quantum wells. <i>Physical Review B</i> , 2011 , 83,	3.3	146

166	Study of efficiency droop and carrier localisation in an InGaN/GaN quantum well structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2194-2196		15
165	Towards predictive modeling of near-edge structures in electron energy-loss spectra of AlN-based ternary alloys. <i>Physical Review B</i> , 2011 , 83,	3.3	33
164	Atom probe tomography assessment of the impact of electron beam exposure on In _x Ga _{1-x} N/GaN quantum wells. <i>Applied Physics Letters</i> , 2011 , 99, 021906	3.4	43
163	A quantitative model for doping contrast in the scanning electron microscope using calculated potential distributions and Monte Carlo simulations. <i>Journal of Applied Physics</i> , 2011 , 109, 013109	2.5	36
162	Microstructural origins of localization in InGaN quantum wells. <i>Journal Physics D: Applied Physics</i> , 2010 , 43, 354003	3	75
161	Dislocation movement in GaN films. <i>Applied Physics Letters</i> , 2010 , 97, 261907	3.4	39
160	Scanning transmission electron microscopy investigation of the Si(111)/AlN interface grown by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2010 , 97, 251901	3.4	45
159	Low temperature photoluminescence and cathodoluminescence studies of nonpolar GaN grown using epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 2010 , 108, 033523	2.5	21
158	Inclined dislocation arrays in AlGaIn/AlGaIn quantum well structures emitting at 290 nm. <i>Journal of Applied Physics</i> , 2010 , 108, 123522	2.5	7
157	Electronic and optical properties of nonpolar a-plane GaN quantum wells. <i>Physical Review B</i> , 2010 , 82,	3.3	33
156	A Direct Method for Charge Collection Probability Computation Using the Reciprocity Theorem. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 2455-2461	2.9	3
155	The effects of annealing on non-polar (1 1 2̄0) a-plane GaN films. <i>Journal of Crystal Growth</i> , 2010 , 312, 3536-3543	1.6	8
154	Dislocation reduction in GaN grown on Si(111) using a strain-driven 3D GaN interlayer. <i>Physica Status Solidi (B): Basic Research</i> , 2010 , 247, 1753-1756	1.3	7
153	Q-factor measurements on planar nitride cavities. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010 , 7, 1866-1868		
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